

# MA6X125

Silicon epitaxial planar type

For switching circuits

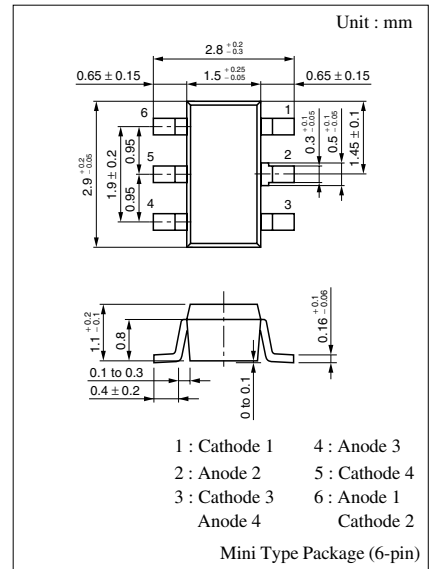
## ■ Features

- Four-element contained in one package, allowing high-density mounting

## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

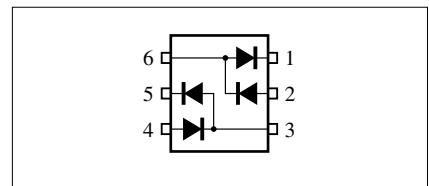
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	40	V
Peak reverse voltage	$V_{RM}$	40	V
Forward current (DC)*	$I_F$	100	mA
Peak forward current*	$I_{FM}$	200	mA
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \*1 : Value for single diode



Marking Symbol: M2I

Internal Connection



## ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 40\text{ V}$			100	nA
Forward voltage (DC)	$V_F$	$I_F = 100\text{ mA}$			1.2	V
Reverse voltage (DC)	$V_R$	$I_R = 100\ \mu\text{A}$	40			V
Terminal capacitance	$C_t$	$V_R = 0\text{ V}, f = 1\text{ MHz}$			5	pF
Reverse recovery time*3	$t_{rr1}$ *1	$I_F = 10\text{ mA}, V_R = 6\text{ V}$		150		ns
	$t_{rr2}$ *2	$I_{rr} = 0.1 \cdot I_R, R_L = 100\ \Omega$		90		

Note) 1. Rated input/output frequency: 100 MHz

2. \*1 : Between pins 1 and 6, Between pins 3 and 5

\*2 : Between pins 2 and 6, Between pins 3 and 4

\*3 :  $t_{rr}$  measuring circuit

